MSD602-RT1G

NPN General Purpose Amplifier Transistor Surface Mount

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Collector−Base Voltage	$V_{(BR)CBO}$	60	Vdc
Collector−Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter−Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current − Continuous	I_C	500	mAdc
Collector Current − Peak	$I_{C(P)}$	1.0	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	−55 ~ +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor®

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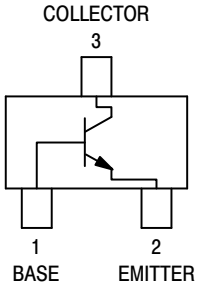
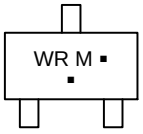
SC−59
CASE 318D
STYLE 1



MARKING DIAGRAM



WR = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MSD−602RT1G	SC−59 (Pb−Free)	3,000 / Tape & Reel
SMSD−602RT1G	SC−59 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Max	Unit
Collector−Emitter Breakdown Voltage (I_C = 10 mA, I_B = 0)	$V_{(BR)CEO}$	50	−	V
Collector−Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$	60	−	V
Emitter−Base Breakdown Voltage (I_E = 10 μA, I_C = 0)	$V_{(BR)EBO}$	7.0	−	V
Collector−Base Cutoff Current (V_{CB} = 20 V, I_E = 0)	I_{CBO}	−	0.1	μA
DC Current Gain (Note 1) (V_{CE} = 10 V, I_C = 150 mA) (V_{CE} = 10 V, I_C = 500 mA)	h_{FE1} h_{FE2}	120 40	240 −	−
Collector−Emitter Saturation Voltage (I_C = 300 mA, I_B = 30 mA)	$V_{CE(sat)}$	−	0.6	V
Base−Emitter On Voltage (I_C = 300 mA, V_{CE} = 5 V)	$V_{BE(on)}$	−	1.0	V
Base−Emitter Saturation Voltage (I_C = 300 mA, I_B = 30 mA)	$V_{BE(sat)}$	−	1.0	V
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1.0 MHz)	C_{ob}	−	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

TYPICAL CHARACTERISTICS

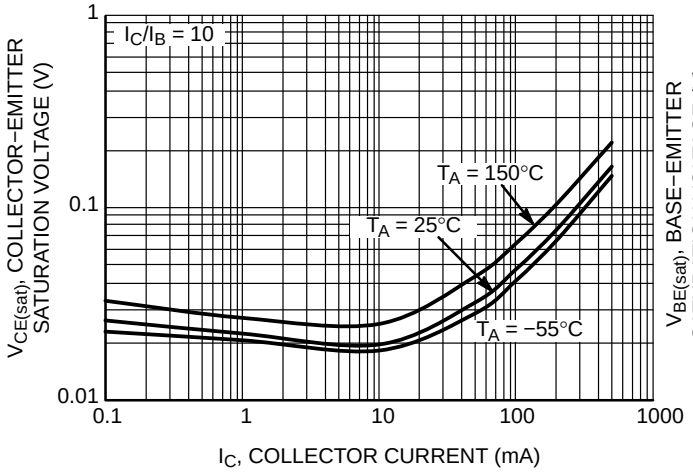


Figure 1. Collector−Emitter Saturation Voltage vs. Collector Current

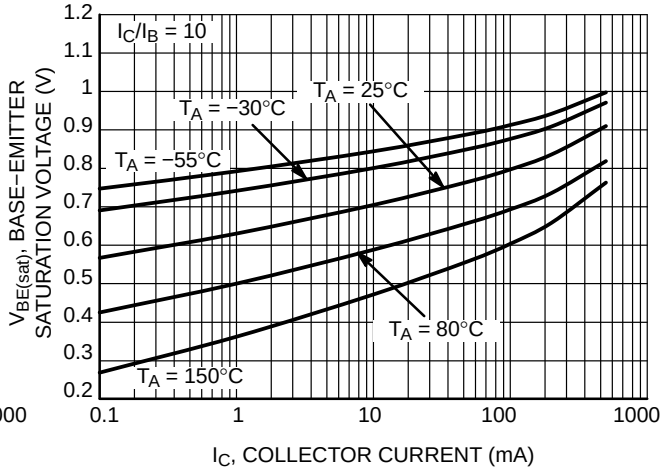


Figure 2. Base−Emitter Saturation Voltage vs. Collector Current

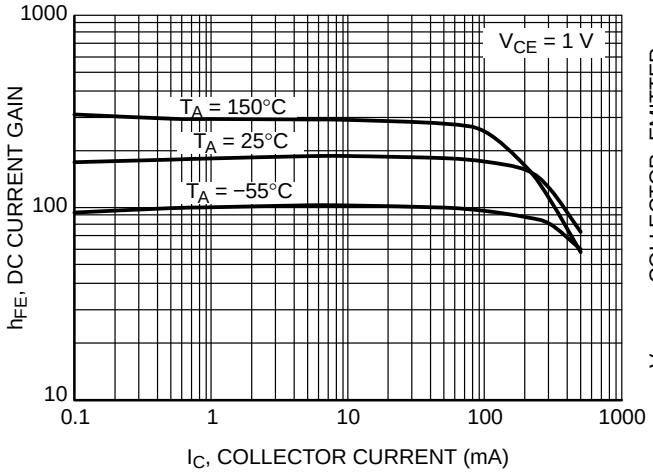


Figure 3. DC Current Gain vs. Collector Current

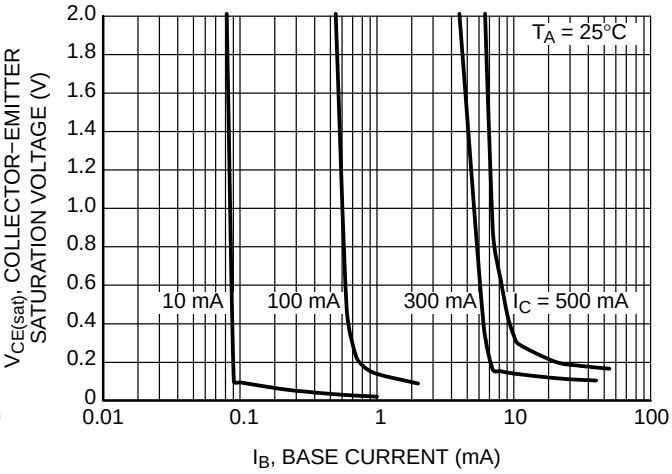


Figure 4. Saturation Region

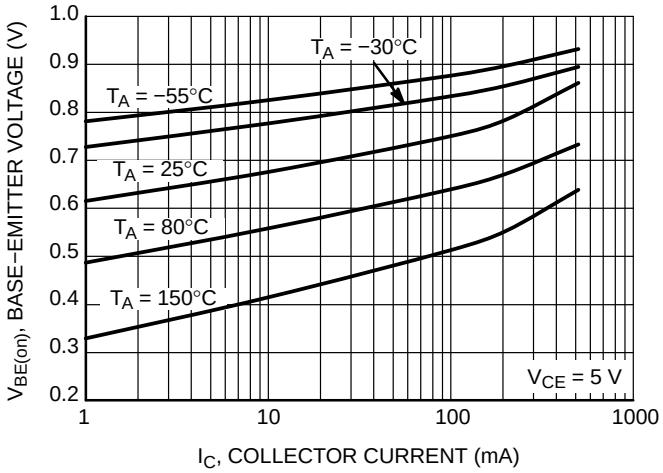


Figure 5. Base−Emitter Turn−On Voltage vs. Collector Current

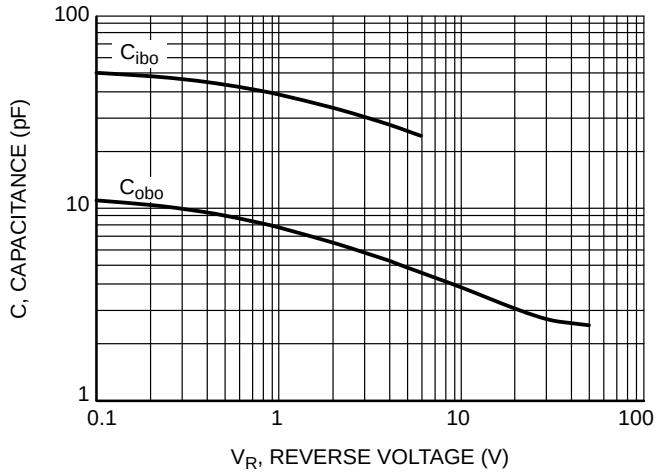


Figure 6. Capacitance

TYPICAL CHARACTERISTICS

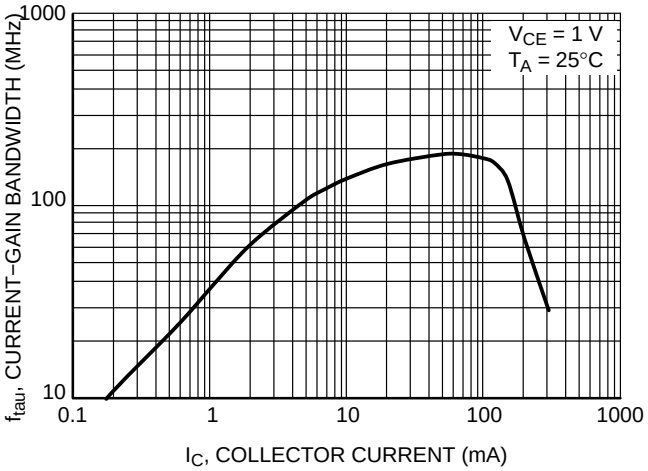


Figure 7. Current Gain Bandwidth Product vs. Collector Current

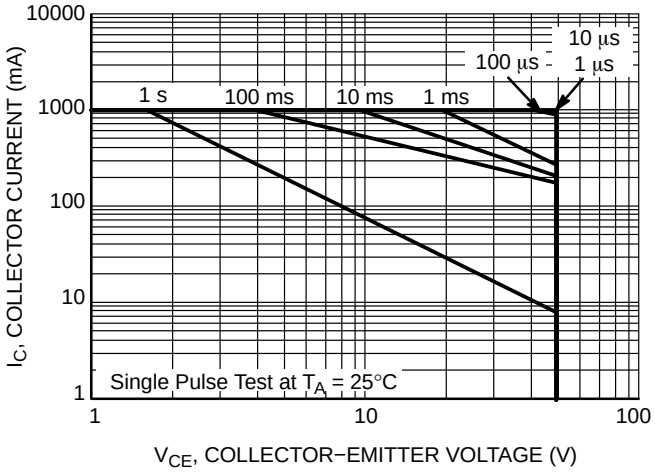


Figure 8. Safe Operating Area

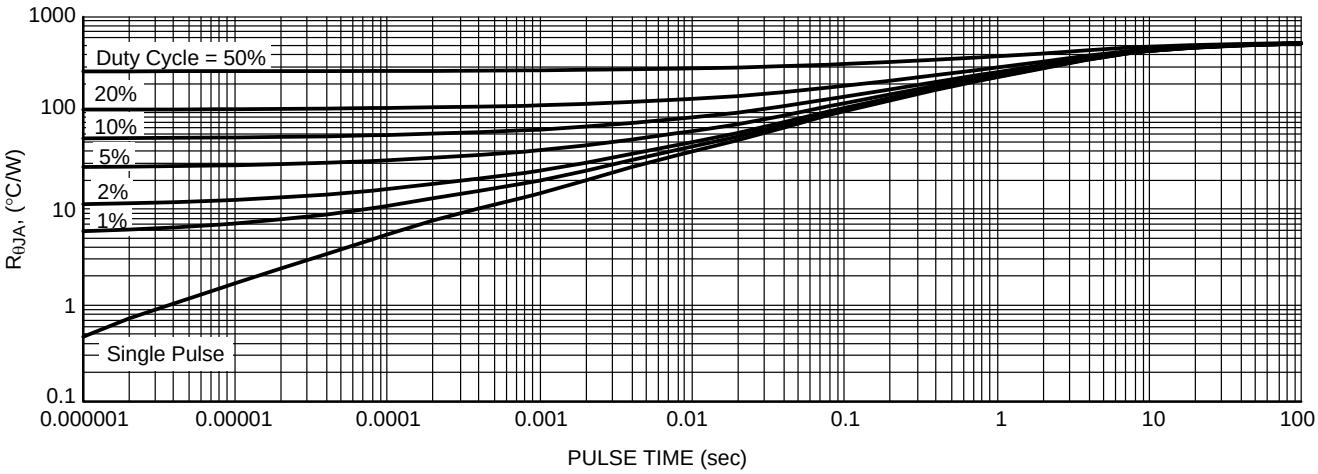
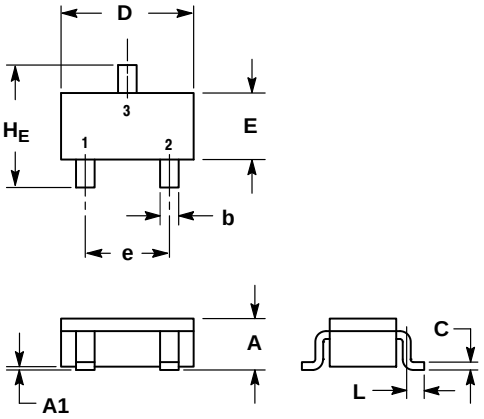


Figure 9. Thermal Response

MSD602−RT1G

PACKAGE DIMENSIONS

SC−59
CASE 318D−04
ISSUE H

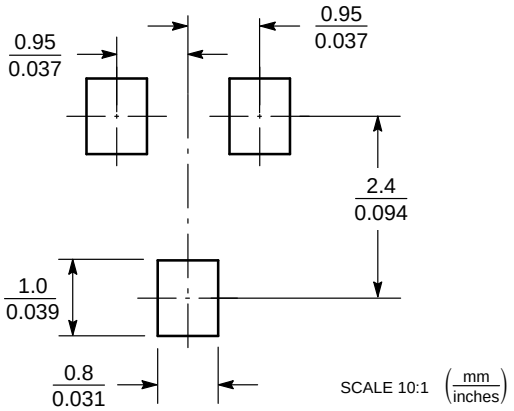


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.80	3.00	0.099	0.110	0.118

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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